

SEMITOP® 2

Antiparallel Thyristor Module

SK 25 WT

Preliminary Data

Features

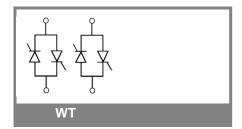
- Compact Design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

Typical Applications

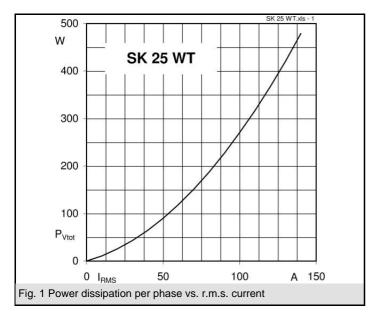
- Soft starters
- Light control (studios, theaters...)
- Temperature control

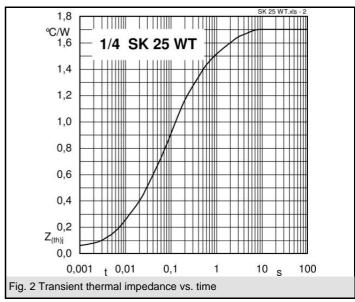
V _{RSM}	V_{RRM}, V_{DRM}	I _{RMS} = 29 A A (full conduction)
V	V	(T _s = 85 °C)
900	800	SK 25 WT 08
1300	1200	SK 25 WT 12
1700	1600	SK 25 WT 16

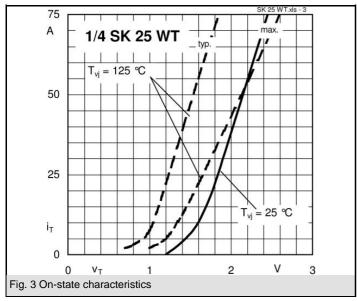
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Symbol	Conditions	Values	Units
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	I _{RMS}	W1C ; sin. 180° ; T _s = 100°C	20	Α
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		W1C ; sin. 180° ; T _s = 85°C	29	Α
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	I _{TSM}	T _{vi} = 25 °C ; 10 ms	320	Α
$\begin{array}{cccccccccccccccccccccccccccccccccccc$			280	Α
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	i²t	$T_{vj} = 25 ^{\circ}\text{C} \; ; 8,310 \text{ ms}$	510	A²s
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		T _{vj} = 125 °C ; 8,310 ms	390	A²s
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	V _T		max. 2,45	1
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$V_{T(TO)}$	T _{vj} = 125 °C	-	V
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	r _T	T _{vj} = 125 °C	max. 20	mΩ
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$I_{DD};I_{RD}$		max. 8	mA
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	t _{gd}	1 ,	1	μs
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	t_{gr}		1	μs
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	(dv/dt) _{cr}		500	V/µs
$\begin{array}{cccccccccccccccccccccccccccccccccccc$				A/µs
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	t_q		80	μs
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	I _H	"	80 / 150	mA
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	I_{L}	ļ ·,	150 / 300	mA
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V_{GT}		min. 2	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	I_{GT}		min. 100	mA
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V_{GD}	T_{vj} = 125 °C; d.c.	max. 0,25	V
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	I_{GD}	T _{vj} = 125 °C; d.c.	max. 3	mA
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	R _{th(i-s)}	cont. per thyristor	1,7	K/W
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	· u · /	sin 180° per thyristor	1,78	K/W
Sin 180° per W1C	$R_{th(j-s)}$	·	0,85	K/W
T _{stg}		sin 180° per W1C	,	
T _{solder} terminals, 10s 260 °C V _{isol} a. c. 50 Hz; r.m.s.; 1 s / 1 min. 3000 / 2500 V~ M _s Mounting torque to heatsink 2,5 Nm M _t a m 19 g	T_{vj}			
V _{isol} a. c. 50 Hz; r.m.s.; 1 s / 1 min. 3000 / 2500 V~ M _s Mounting torque to heatsink 2,5 Nm M _t Nm Nm Nm a 19 g	T_{stg}		-40 +12 5	
V _{isol} a. c. 50 Hz; r.m.s.; 1 s / 1 min. 3000 / 2500 V~ M _s Mounting torque to heatsink 2,5 Nm Nm Nm nm 19 g	T _{solder}	terminals, 10s	260	°C
M _s Mounting torque to heatsink 2,5 Nm M _t Nm Nm Nm a m 19 g	V _{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 / 2500	V~
m m/s² g	M_s	Mounting torque to heatsink	2,5	Nm
m 19 g	M_t			Nm
	а			m/s²
Case SEMITOP® 2 T 37	m		19	g
	Case	SEMITOP® 2	T 37	

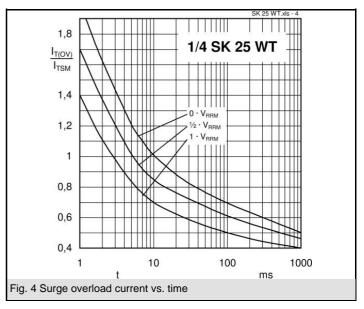


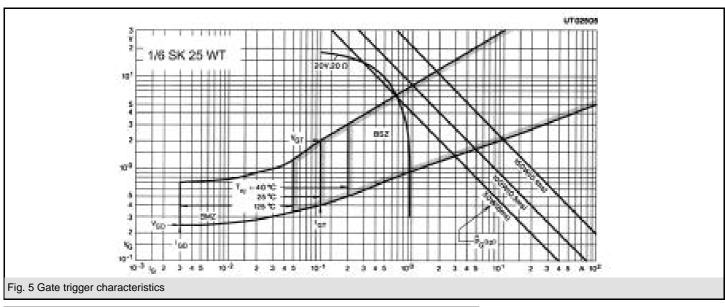
SK 25 WT

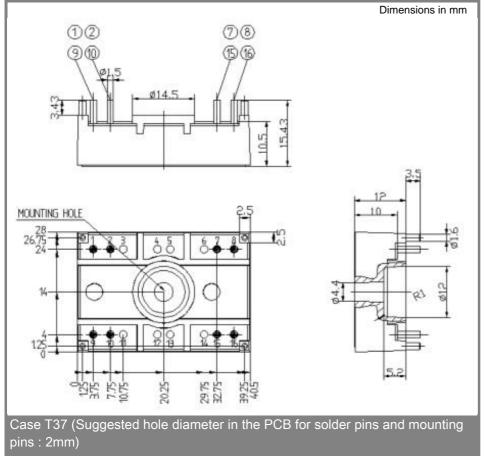


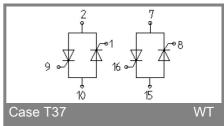












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